Part Number	Customer

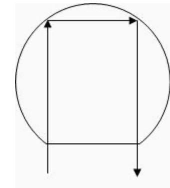
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	200.00 +/- 0.30 mm	
	2.0	Notch or Flat	57.50 +/- 2.50 mm	Wafer Vendor
	3.0	Notch Direction	<110> +/- 1 degree	Wafer Vendor
	4.0	Overall Thickness	745.00 +/- 26.00 µm	ADE, 100%
	5.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<100.00µm	ADE to ASTM F534, 100%
	8.0	Warp	<100.00µm	
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5 mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	14.0	Handle Thickness	725.00 +/- 25.00 µm	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Phosphorous	Wafer Vendor
	17.0	Handle Resistivity	1-200 Ohmcm	Wafer Vendor
	18.0	Resistivity variation (within wafer)	<15.00%	wafer vendor
	21.0	Backside Finish	Lap/Etch with oxide and no lasermark	Wafer Vendor
BuriedOxide	22.0	Oxide Type	Thermal	
	23.0	Oxide Thickness	50,000.00 +/- 2,500.00 A	Nanospec centre point, 4%
	24.0	Oxide formed on	3 um on Handle and 2 um on Device Wafers	
DeviceSilicon	25.0	Device Growth Method	CZ	Wafer Vendor
	26.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	27.0	Nominal Thickness	15.00 +/- 1.00 µm	FTIR, 100% 9-Pt (note3)
	28.0	Distance to device silicon edge from wafer edge	<= 1.5mm	defined edge
	29.0	Device Doping Type	N	Wafer Vendor
	30.0	Device Dopant	Phosphorous	Wafer Vendor
	31.0	Device Resistivity	36-54 Ohmcm	Wafer Vendor
	32.0	Resisitivity variation (within wafer)	<10.00%	Wafer Vendor
	33.0	Buried Layer Implant	Sb/80keV/1e12 cm3	Wafer Vendor
	35.0	Voids	none	Wafer Vendor
	36.0	Scratches	0	Bright Light, 100% (note 2)
	37.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

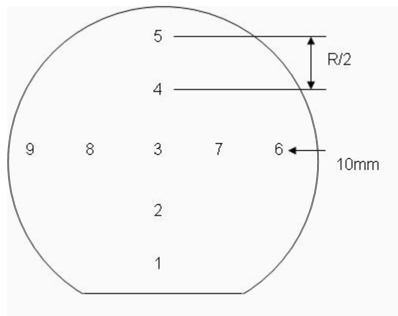
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information